

30V Dual P-Channel MOSFET



SOP-8

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Pin Definition:

1. Source 1 2. Gate 1	8. Drain 7
3. Source 2	6. Drain 2
4. Gate 2	5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
	60 @ V _{GS} = 10V	-4.9
-30	90 @ V _{GS} = 4.5V	-3.7

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

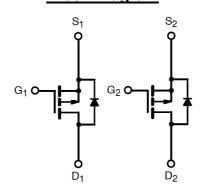
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM4953DCS RL	SOP-8	2.5Kpcs / 13" Reel
TSM4953DCS RLG	SOP-8	2.5Kpcs / 13" Reel

Note: "G" denotes Halogen Free Product.

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	-4.9	А	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-20	А	
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	-2.6	А	
Maximum Power Dissipation	Ta = 25°C	P _D	2.5	W	
	Ta = 70°C		1.3		
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T_{J}, T_{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JC}$	40	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	62.5	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.



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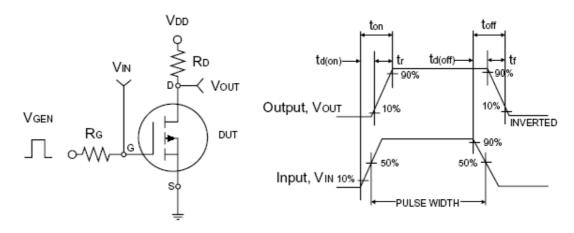


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V _{GS(TH)}	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current ^a	V _{DS} =-5V, V _{GS} = -10V	I _{D(ON)}	-6			Α
Drain-Source On-State Resistance ^a	$V_{GS} = -10V, I_D = -4.9A$	_		50	60	mΩ
	$V_{GS} = -4.5V, I_D = -3.7A$	$R_{DS(ON)}$		75	90	
Forward Transconductance ^a	$V_{DS} = -15V, I_{D} = -4.9A$	g fs		10		S
Diode Forward Voltage	I _S = -1.9A, V _{GS} = 0V	V _{SD}			-1.3	V
Dynamic						
Total Gate Charge		Q_g		28		
Gate-Source Charge	$V_{DS} = -15V, I_{D} = -4.9A,$ $V_{GS} = -10V$	Q_{gs}		3		nC
Gate-Drain Charge		Q_{gd}		7		
Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		745		
Output Capacitance		C _{oss}		440		pF
Reverse Transfer Capacitance		C _{rss}		120		
Switching						
Turn-On Delay Time	$V_{DD} = -15V, R_L = 15\Omega,$ $I_D = -1A, V_{GEN} = -10V,$ $R_G = 6\Omega$	t _{d(on)}		9		
Turn-On Rise Time		t _r		15		C
Turn-Off Delay Time		t _{d(off)}		75		nS
Turn-Off Fall Time		t _f	-	40		

Notes:

- 1. pulse test: PW ≤300µS, duty cycle ≤2%
- 2. For DESIGN AID ONLY, not subject to production testing.
- 3. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

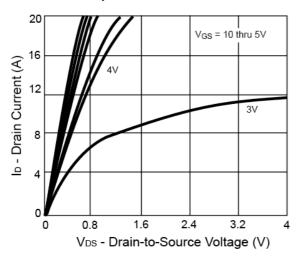


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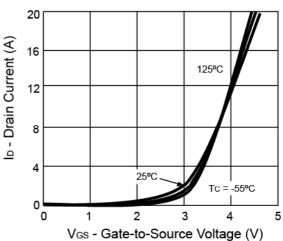


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

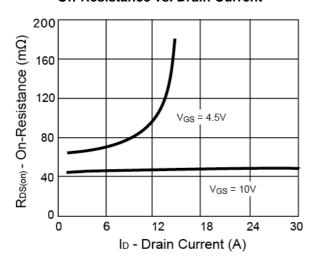
Output Characteristics



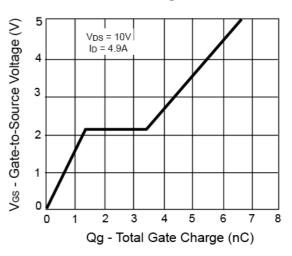
Transfer Characteristics



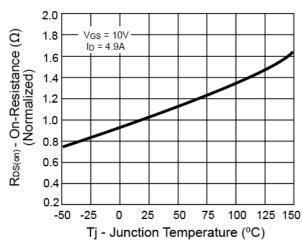
On-Resistance vs. Drain Current



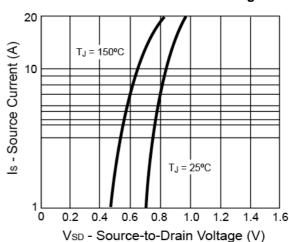
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



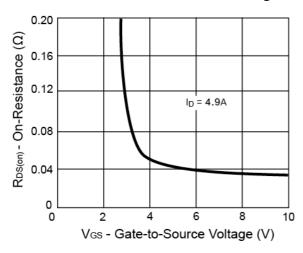


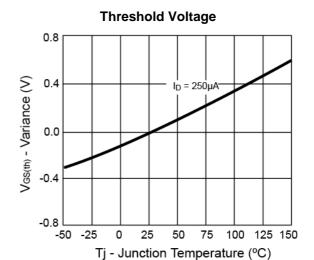
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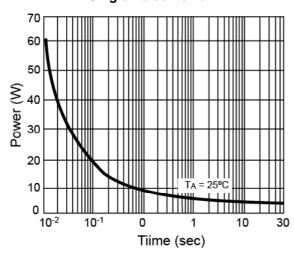
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

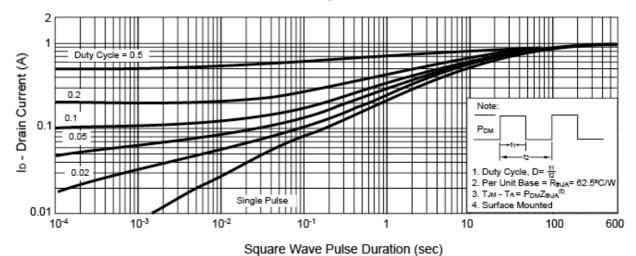




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

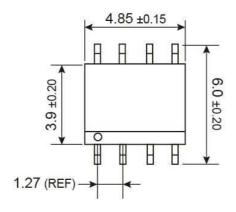


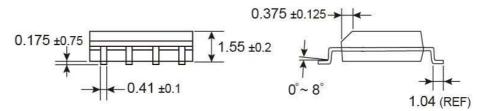






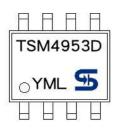
SOP-8 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

= Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code



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